

FIG.1

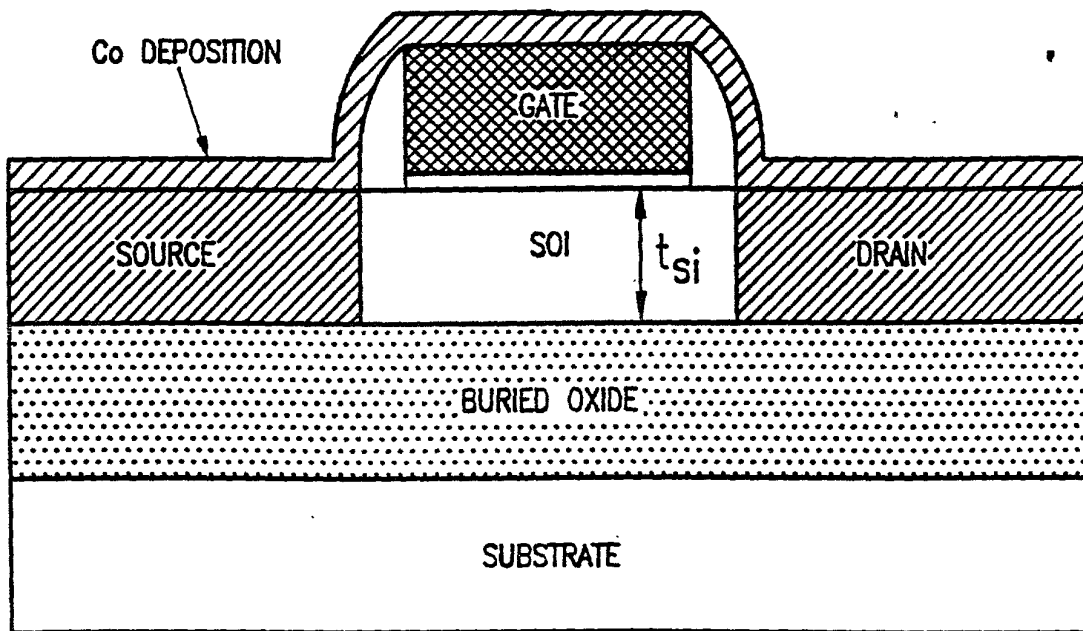


FIG.2

09902483-071101

FORM Co_2Si BY LOW TEMPERATURE ANNEAL

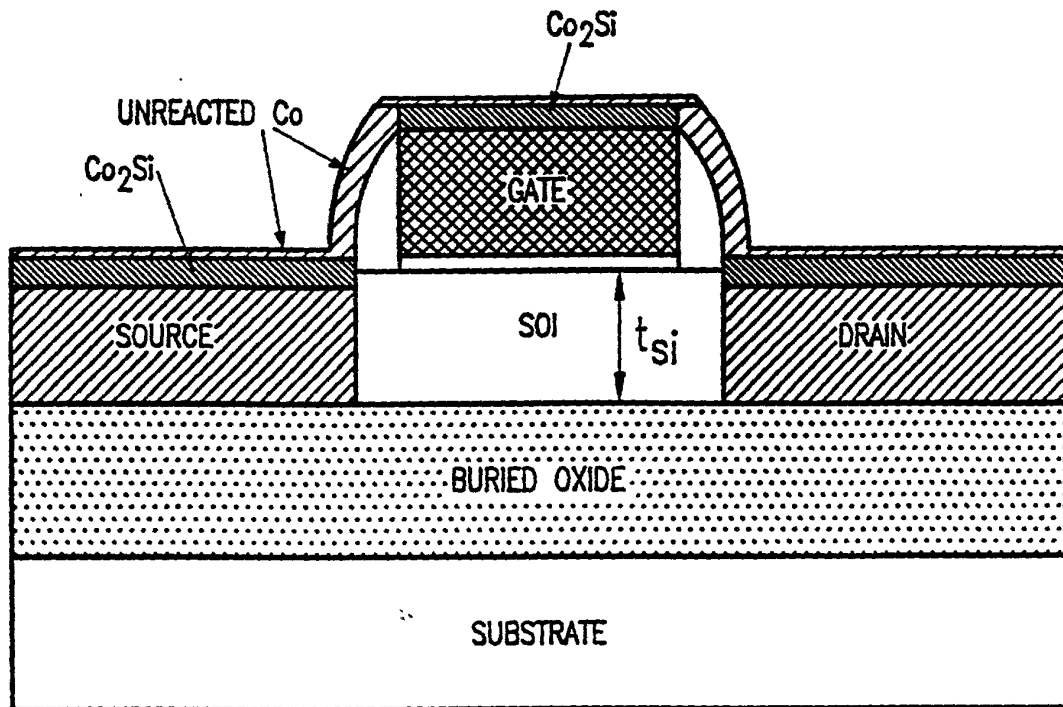


FIG.3

DEPOSITE $\alpha\text{-Si}$

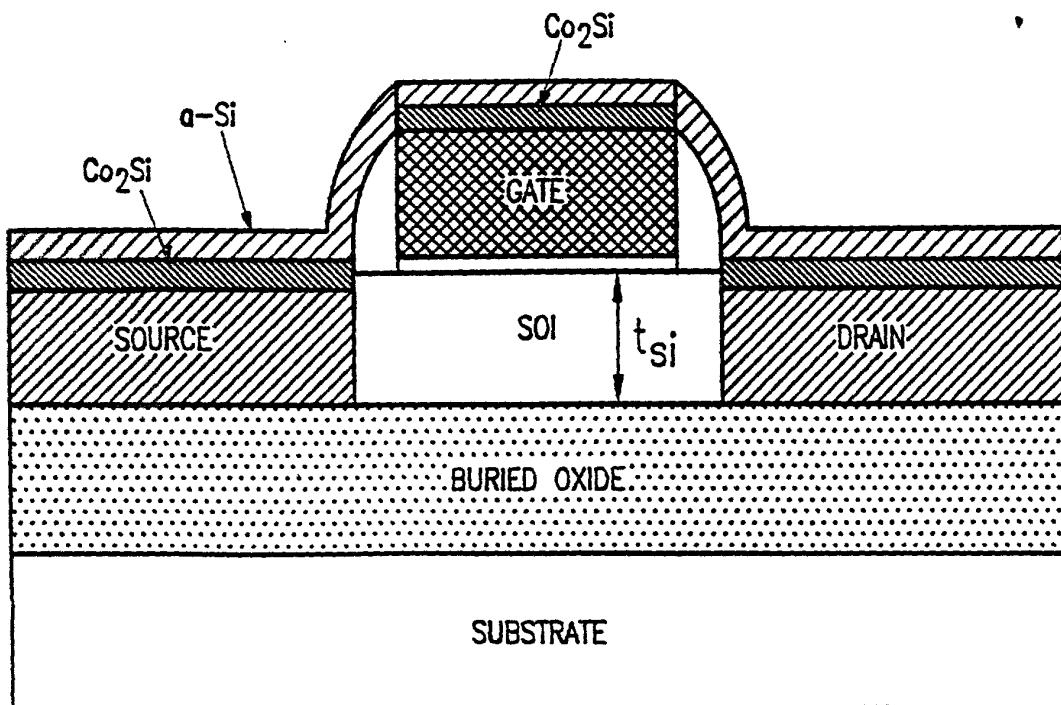


FIG.4

05902483-071104
F01T20" E3420650

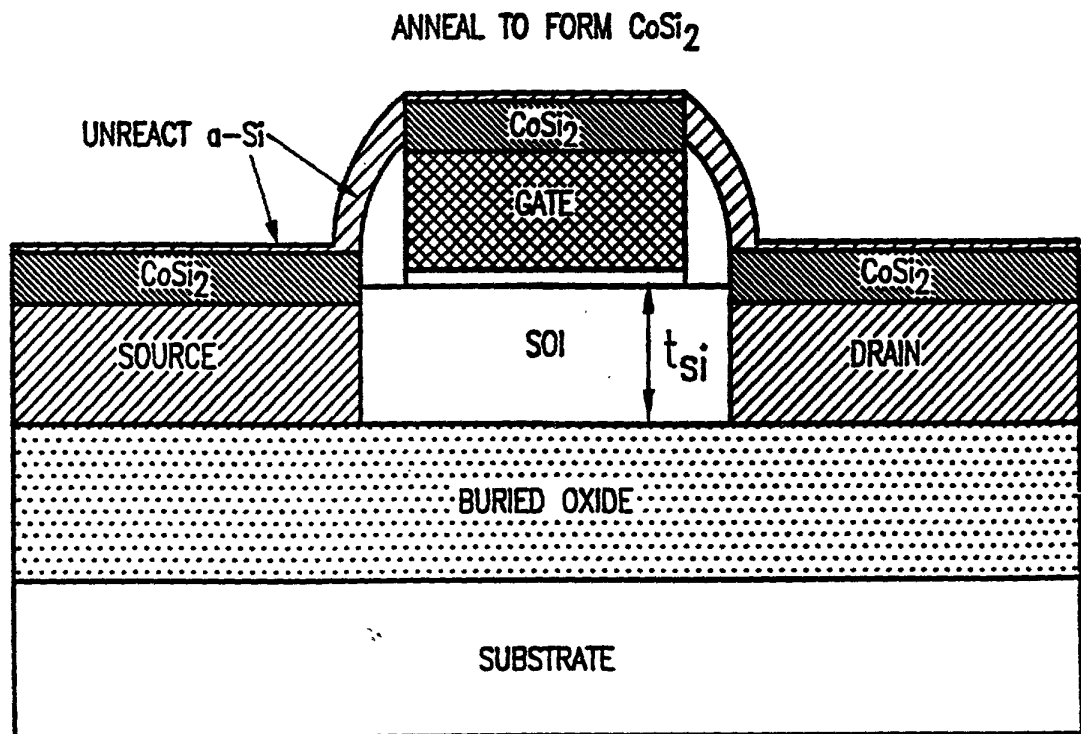


FIG.5

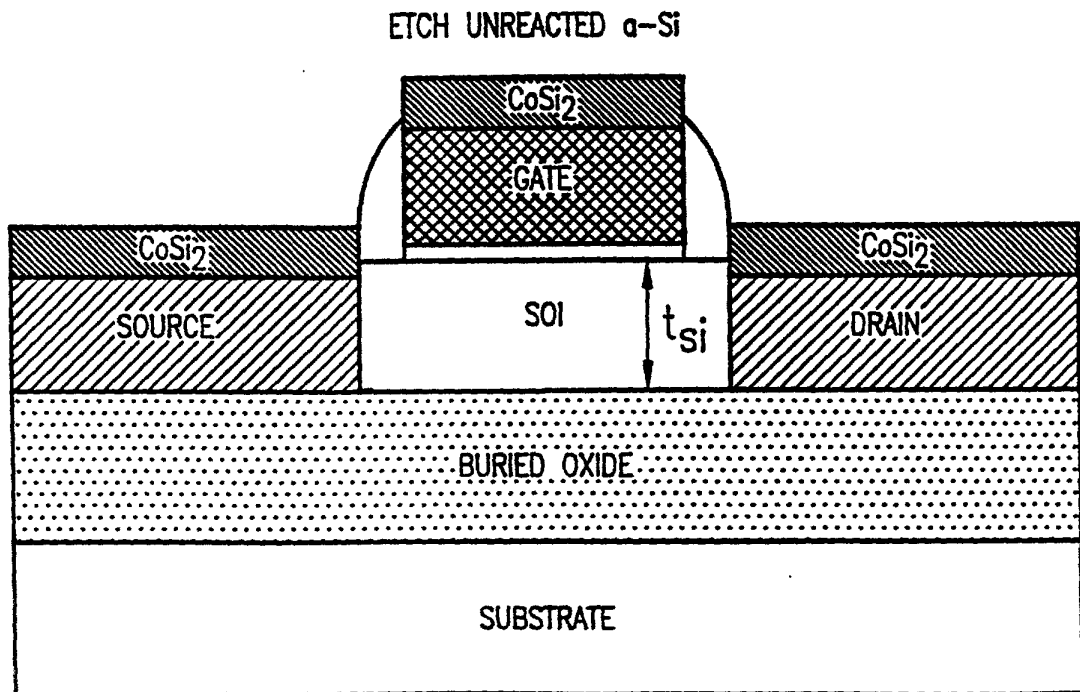
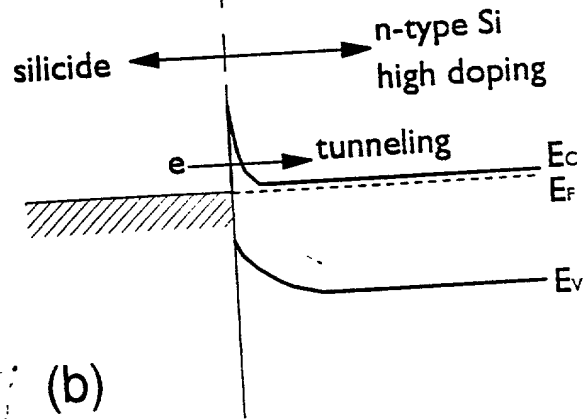
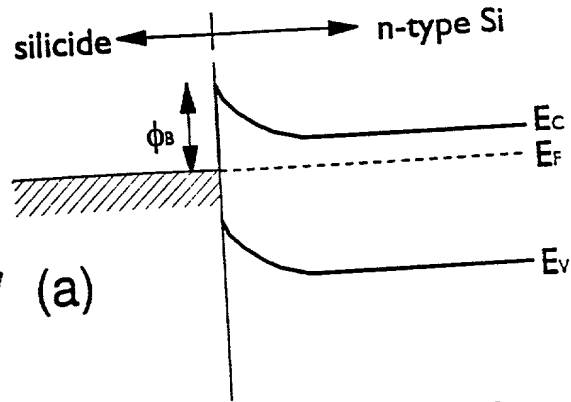
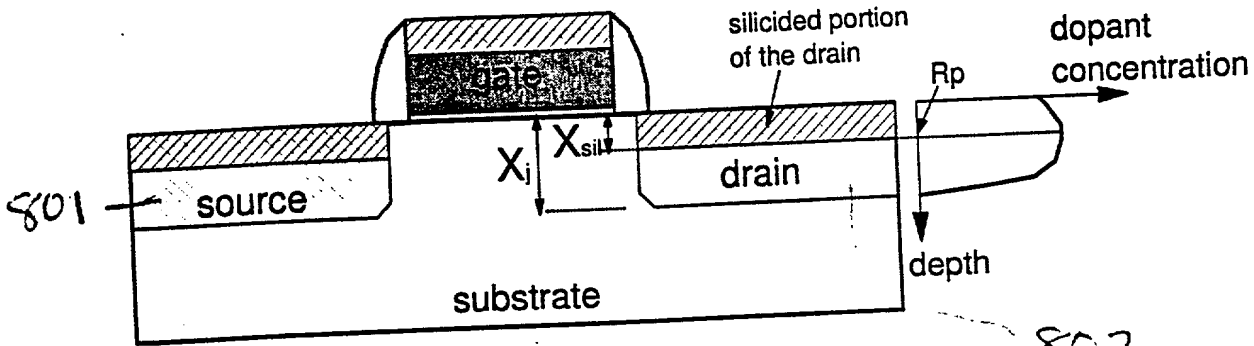


FIG.6



09902493-074104
TOT 120" C0420650

800



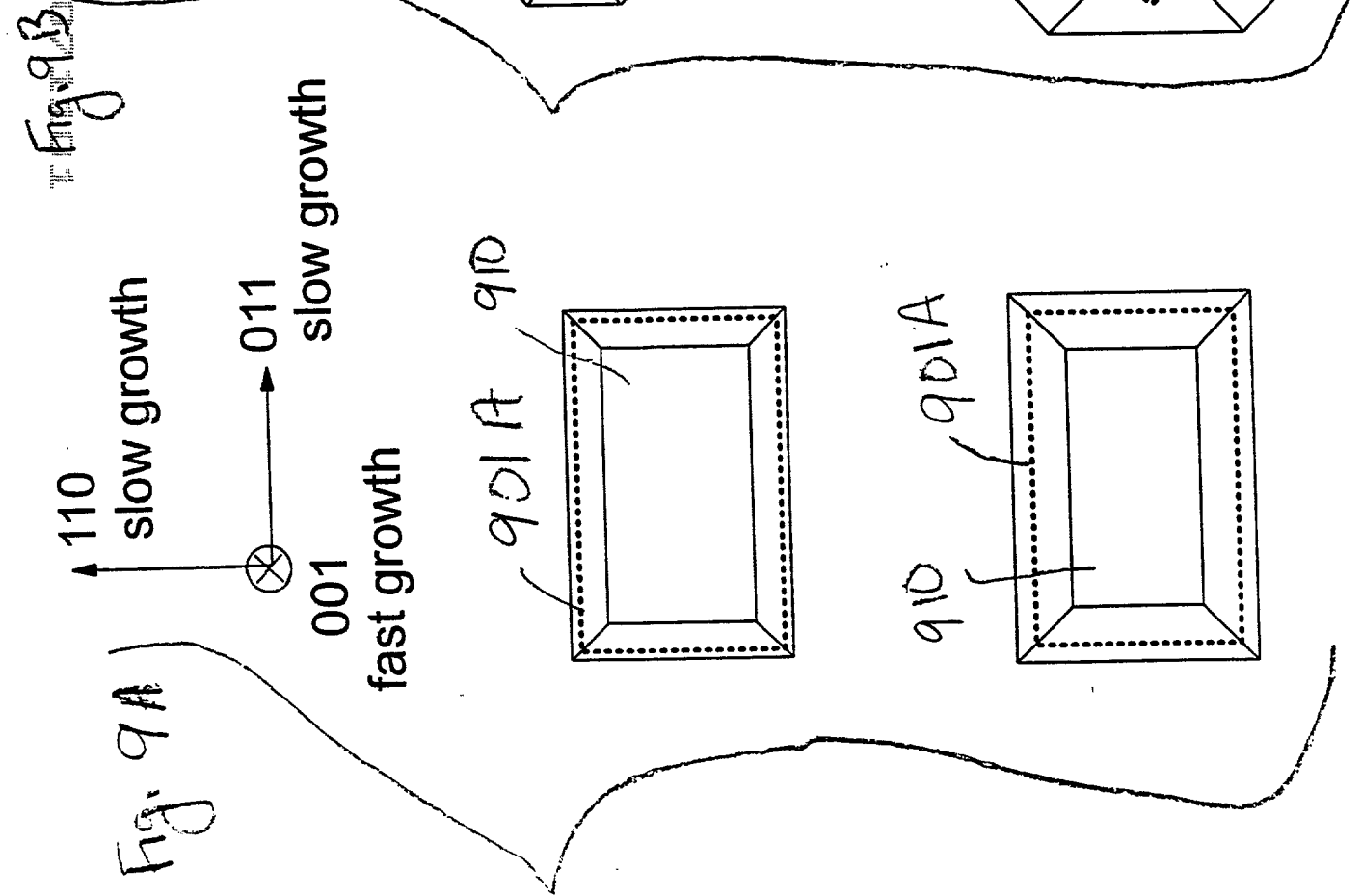
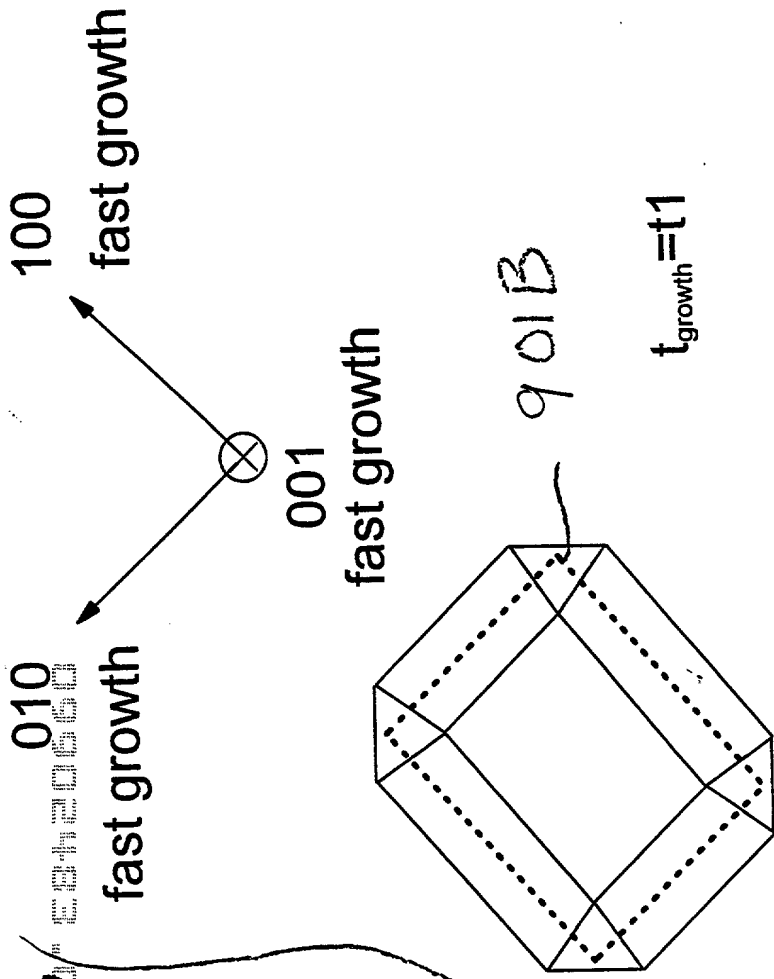
X_j = source or drain junction depth
 X_{sil} = silicide junction depth
 R_p = peak dopant concentration

Requirements:

1. $X_j > X_{sil}$
2. X_{sil} roughly equals R_p

Figure 8

0590483-071104



The dashed line shows the initial growth window which is defined by the hard mask